# 1.8V Drive Nch+Nch MOSFET

### EM6K6

#### Structure

Silicon N-channel MOSFET

#### Applications

Switching

#### ● Features

- 1) The MOSFET elements are independent, eliminating mutual interference.
- 2) Mounting cost and area can be cut in half.
- 3) Low on-resistance.
- 4) Low voltage drive (1.8V) makes this device ideal for portable equipment.

#### Packaging specifications

Туре	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
EM6K6		0

#### ● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2>

Parameter		Symbol	Limits	Unit	
Drain-source voltage		Voss	20	V	
Gate-source voltage		Vgss	±8	V	
Drain current	Continuous	ΙD	±300	mA	
	Pulsed	IDP *1	±600	mA	
Total power dissipation		Pp*2	150	mW / TOTAL	
		PD	120	mW / ELEMENT	
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

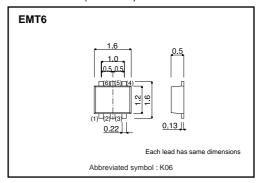
<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

#### ●Thermal resistance

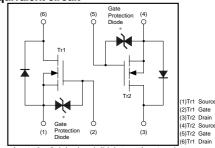
Parameter	Symbol	Limits	Unit		
Channel to ambient	Pth(ch-a)*	833	°C/W / TOTAL		
Charmer to ambient	Kui(cii-a)	Rth(ch-a)* 1042 °C/			

<sup>\*</sup> Each terminal mounted on a recommended land

#### ●Dimensions (Unit: mm)



#### ●Equivalent circuit



A protection diode has been built in between the gate and the source to protect against static electricity when the product is in use. Use the protection circuit when rated voltages are exceeded.

<sup>\*2</sup> Each terminal mounted on a recommended land.

#### ●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μΑ	Vgs=±8V, Vps=0V
Drain-source breakdown voltage	V(BR)DSS	20	-	-	V	In=1mA, Vgs=0V
Zero gate voltage drain current	IDSS	-	_	1.0	μΑ	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS(th)	0.3	_	1.0	V	VDS=10V, ID=1mA
Otatio Indiana and and		-	0.7	1.0	Ω	In=300mA, Vgs=4.0V
Static drain-source on-state resistance	RDS(on)*	_	0.8	1.2	Ω	In=300mA, Vgs=2.5V
		_	1.0	1.4	Ω	In=300mA, Vgs=1.8V
Forward transfer admittance	Yfs  *	400	_	_	ms	In=300mA, Vns=10V
Input capacitance	Ciss	-	25	-	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	-	10	-	pF	Vgs=0V
Reverse transfer capacitance	Crss	-	10	-	pF	f=1MHz
Turn-on delay time	td(on) *	-	5	-	ns	ID=150mA, VDD ≒10V
Rise time	tr *	_	10	_	ns	V <sub>G</sub> S=4.0V
Turn-off delay time	td(off) *	_	15	_	ns	RL=67Ω
Fall time	t <sub>f</sub> *	_	10	_	ns	R <sub>G</sub> =10Ω

<sup>\*</sup> Pulsed

#### ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.2	V	Is= 100mA, V <sub>GS</sub> =0V

<sup>\*</sup> Pulsed

#### •Electrical characteristic curves

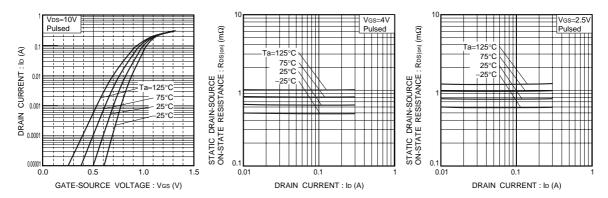


Fig.1 Typical transfer characteristics

Fig.2 Static drain-source on-state resistance vs. drain current (I)

Fig.3 Static drain-source on-state resistance vs. drain current (II)

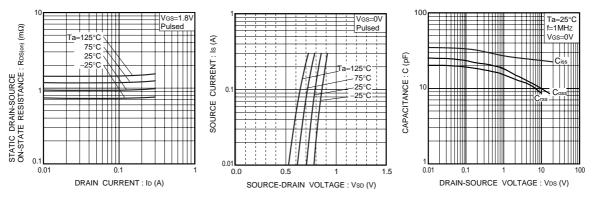


Fig.4 Static drain-source on-state resistance vs. drain current (III)

Fig.5 Source current vs. source-drain voltage

Fig.6 Typical capacitance vs. drain-source voltage

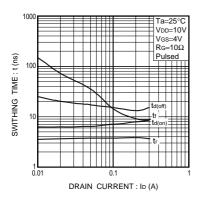


Fig.7 Switching characteristics

#### •Switching characteristics measurement circuit

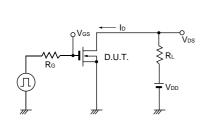


Fig.8 Switching time measurement circuit

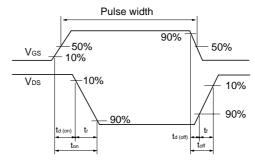


Fig.9 Switching time waveforms

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